

Electrical Test

tesera
V550

- ▶ DFT
- ▶ Scan chain debug
- ▶ Curve Tracer, etc.

MU-TEST

Multi-purpose ATE Tester

- ▶ High Performances
- ▶ Up to 1344 channels
- ▶ High speed 1.6 Gbit, APG for DDR2/3 test, mixed signal channels, VI channels

M-5S

M-21S

FTI-1000

Focused Test, Inc.

Power Discrete, IGBT, GaN-SiC, Analog IC Tester

FEI ELITE

Resistive defects localization

Real Time Lock-in Thermography

Systems

- ▶ Power Modules
- ▶ 3D localization
- ▶ Transient analysis
- ▶ Thermal mapping
- ▶ Improved sensitivity of the new camera (3X)

Packages

- ▶ Through package
- ▶ Silicon

ZEISS Xradia

VersaXRM 410, 510, 520

X-Ray Microscope

- ▶ 3D True resolution
- ▶ 0.7 μm resolution at distance
- ▶ Best absorption and phase contrast
- ▶ 300 mm wafer capability
- ▶ 4D and in-situ analysis

Defects are large

Defects are small

TeraView

EOTPR

TeraHertz TDR

- ▶ Detects opens, shorts: partial cracks, narrowings, constrictions
- ▶ 5 μm spatial resolution

Insight k.k.

IS-250, IS-350

Scanning Acoustic Microscope

- ▶ Wide application range
- ▶ 0.1 μm spatial resolution
- ▶ High speed technology
- ▶ Compact size

RAY

Decap 10

Fiber Laser Ablation

20 W pulsed fiber laser

- ▶ For fast and reproducible package pre-opening

Nisene

JetEtch Pro

CuProtect

Total Protect

- ▶ Protect copper from corrosion
- ▶ Electrolytic chamber
- ▶ Temperature control

Acid Decapsulation

Nisene

Plasma Etch

- ▶ Acid-free, low temperature
- ▶ Focused/ isotropic etching
- ▶ Latest solution for silver wires and complex packages

Precision Milling

varioscale

VarioMill

- ▶ For ultimate silicon backside thinning

Metrology

varioscale

VarioMetric

- ▶ High precision laser-based thickness measurements

SEIWA OPTICAL

NIR Imaging

- ▶ To improve sensitivity of your EMMI tools
- ▶ To optimize laser transmission
- ▶ For generic use (Microscopes, NUV/ IR lenses)

Lens	20x	50x	100x
NA	0.6	0.7	0.75
WD	10 mm	10 mm	10 mm
Transmission	>70% (1 μm -2 μm)	>70% (1 μm -2 μm)	>80% (1 μm -1.6 μm)

FEI

EFA

- ▶ Standard application (EMMI, OBIRCh)
- ▶ New Technologies (LVx, High NA SIL)

Meridian IV

Waferscan WS-DP

Meridian M

The most comprehensive platform for Electrical Failure Analysis (EFA)

- ▶ Emission Microscopy, OBIRCh, Laser Voltage Imaging & Probing
- ▶ Down to 14nm technology node, High NA SIL imaging
- ▶ Low noise, high sensitivity, extended-wavelength "next generation" camera (DBx)
- ▶ Waferscan— Wafer level FA due to semi-automated wafer prober

FEI

ELITE

Thermal Emission

- ▶ Sensitivity & Resolution

Lock-in thermography system for resistive defects localization

- ▶ SIL lenses
- ▶ High-Doped Silicon Lens
- ▶ Thermal mapping
- ▶ New high-speed camera and SW

FEI

nProber II

Hyperion

NanoProbing

- ▶ Efficiency toward electrical analysis

Transistor probing on sub-14 nm nodes devices

- ▶ up to 8 encoded nanoprobes, HR SEM imaging
- ▶ Electron Beam Induced/Absorbed Current (EBIC/EBAC)
- ▶ up to 8 encoded nanoprobes, HR AFM imaging
- ▶ PicoCurrent™, Scanning Capacitance modes
- ▶ Dynamic characterization capability (Pulsed IV)

FEI

Meridian V

Dynamic FA

- ▶ Timing & Functional Analysis

Proven on 14 nm technology node

- ▶ Optimized dynamic LSM platform
- ▶ LVI, LVP, OBIRCh, Soft Defect Localization
- ▶ Design Debug
- ▶ Highest performance High NA SIL and imaging

FEI

OptiFIB Taipan

Circuit Edit

- ▶ Front-side / Back-side FIB

Down to 10 nm technology

- ▶ Broadest range of chemistries
- ▶ New coaxial ion-photon column
- ▶ Excellent navigation and ion beam placement

FEI

Silicon Die FA

14nm

ISO9001 certified

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Providing Effective Solutions...